

# Agenda

Time	Presenter	Institute	Title of Presentation
9:00	T. Mikolajick/ U. Schroeder	Namlab	Welcome

<b>Device</b>		<i>chair: U. Schroeder</i>	
1	9:15 <a href="#">E. Erben</a>	GlobalFoundries	HKMG Reliability
2	9:35 <a href="#">M. Drescher</a>	Fraunhofer IPMS-CNT	Surface treatments for enhanced reliability in 28nm HKMG
3	9:55 <a href="#">D. Triyoso</a>	GlobalFoundries	ALD Spacer for HKMG
4	10:15 <a href="#">M. Tallarida</a>	BTU Cottbus	III-V/Oxide Interfaces Investigated with Synchrotron Radiation PE Spectroscopy
5	10:35 <a href="#">A. Freese</a>	Namlab	Molecular beam deposited ZrO <sub>2</sub> as a high k dielectric for future GaN power devices

Coffee break: 10:50 - 11:10h

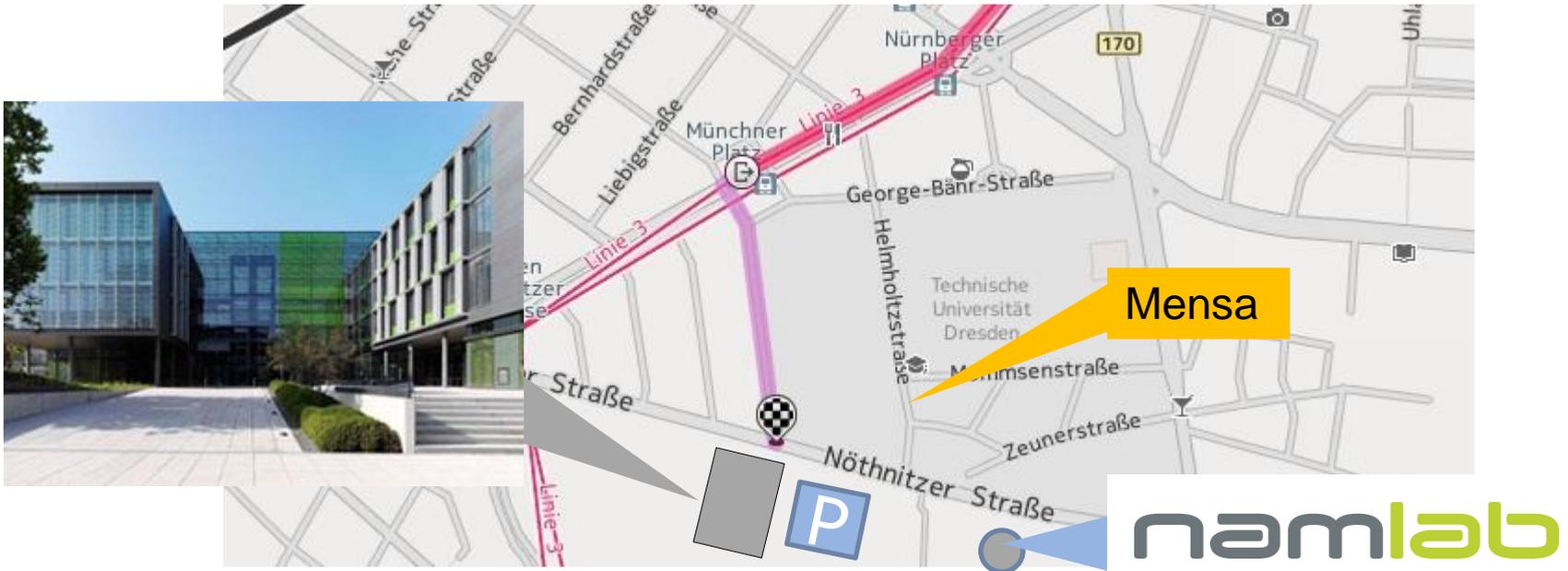
<b>Non volatile memory</b>		<i>chair: U. Schroeder</i>	
6	11:10 P. Polakowski	Fraunhofer IPMS-CNT	Alternative dopants for stabilizing Ferroelectric HfO <sub>2</sub> in planar MIM-stacks
7	11:30 <a href="#">T. Schenk</a>	Namlab	Electric Field Cycling Behavior of Ferroelectric Sr:HfO <sub>2</sub>
8	11:45 <a href="#">S. Starschich</a>	RWTH Aachen IWE2	Low temperature switching behavior of doped HfO <sub>2</sub>
9	12:05 <a href="#">R. Materlik</a>	Hochschule München	Simulation of ferroelectric doped HfO <sub>2</sub>

Lunch - Alte Mensa (Helmholtz Strasse): 12:25 - 13:30h

# Enjoy Lunch☺

For your lunch ticket you will get:

- one main dish
- + one dessert
- + one drink



# Agenda

Lunch - Alte Mensa (Helmholtz Strasse): 12:25 - 13:30h

## RRAM

*chair: S. Slesazeck*

- |    |       |                             |                    |  |
|----|-------|-----------------------------|--------------------|--|
| 10 | 13:30 | <a href="#">T. Bertaud</a>  | IHP Frankfurt/Oder | HfO <sub>2</sub> based RRAM for embedded non-volatile memory   |
| 11 | 13:50 | U. Böttger                  | RWTH Aachen IWE2   | From soft breakdown to resistive switching   |
| 12 | 14:10 | <a href="#">S. Spiga</a>    | MDM Agrate Brianza | Resistive switching in doped-HfO <sub>2</sub>  |
| 13 | 14:30 | <a href="#">K. Fröhlich</a> | U. Bratislava      | Resistive switching in oxide based metal-insulator-metal structures: TiO <sub>2</sub> , HfO <sub>2</sub> |
| 14 | 14:50 | <a href="#">H. Wylezich</a> | Namlab             | Tuning Nb <sub>2</sub> O <sub>5</sub> for Resistive Switching by Ion Implantation                        |

## Capacitor

- |    |       |                              |                     |  |
|----|-------|------------------------------|---------------------|--|
| 15 | 15:05 | <a href="#">W. Weinreich</a> | Fraunhofer IPMS-CNT | 3D MIM Capacitors with improved reliability for SoC and SiP applications |
|----|-------|------------------------------|---------------------|--|

Coffee break: 15:25 - 15:45h

## Solar/OLED

*chair: I. Dirnstorfer*

- |    |       |                             |               |   |
|----|-------|-----------------------------|---------------|---|
| 16 | 15:45 | <a href="#">E. Kessels</a>  | TU Eindhoven  | ALD of oxides for silicon photovoltaics   |
| 17 | 16:05 | <a href="#">A. Schmid</a>   | TUBA Freiberg | Defect characterization and passivation characteristics of high k materials                       |
| 18 | 16:25 | <a href="#">F. Benner</a>   | Namlab        | Effects of Ti-doping on the passivation effect of Al <sub>2</sub> O <sub>3</sub> thin film layers |
| 19 | 16:40 | <a href="#">C. Hossbach</a> | IHM           | ALD and MLD barrier layers for OLED and OPV   |

17:00 End